

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al. Examiner: Ly D. Pham
Serial No.: Unknown Group Art Unit: Unknown
Filed: Herewith Docket: 1303.024US2
Title: INTEGRATED CIRCUIT MEMORY DEVICE AND METHOD

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 09/945498, filed on August 30, 2001, which is relied upon for an earlier filing date under 35 U.S.C. §120.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

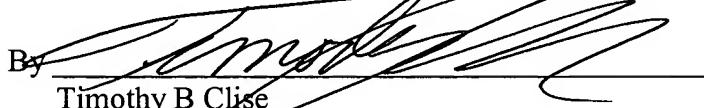
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%;">Application Number</td> <td colspan="4">Unknown</td> </tr> <tr> <td>Filing Date</td> <td colspan="4">Even Date Herewith</td> </tr> <tr> <td>First Named Inventor</td> <td colspan="4">Forbes, Leonard</td> </tr> <tr> <td>Group Art Unit</td> <td colspan="4">Unknown</td> </tr> <tr> <td>Examiner Name</td> <td colspan="4">Pham, Ly</td> </tr> </table>					Application Number	Unknown				Filing Date	Even Date Herewith				First Named Inventor	Forbes, Leonard				Group Art Unit	Unknown				Examiner Name	Pham, Ly			
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		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown
		Examiner Name	Pham, Ly
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